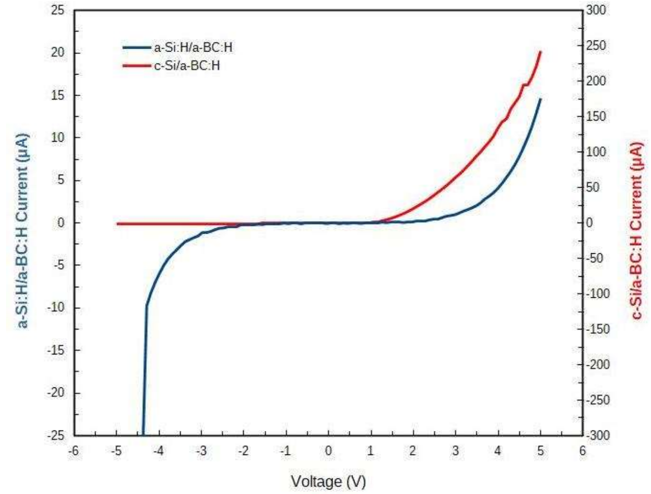

Figure 1 V-I characterstics of a-Si:H(p)/a-BC:H(n) (left vertical axis) and c-Si(p)/a-BC:H(n) (right vertical axis) devices

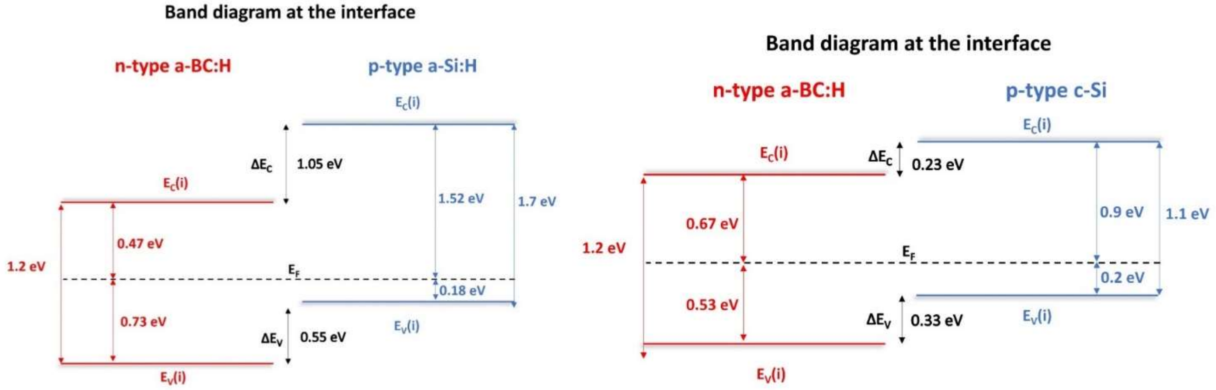

Figure 2 The a-BC:H(n)/a-Si:H(p) heterojunction band diagram at the interface (left) and the a-BC:H(n)/c-Si(p) heterojunction band diagram at the interface (right)

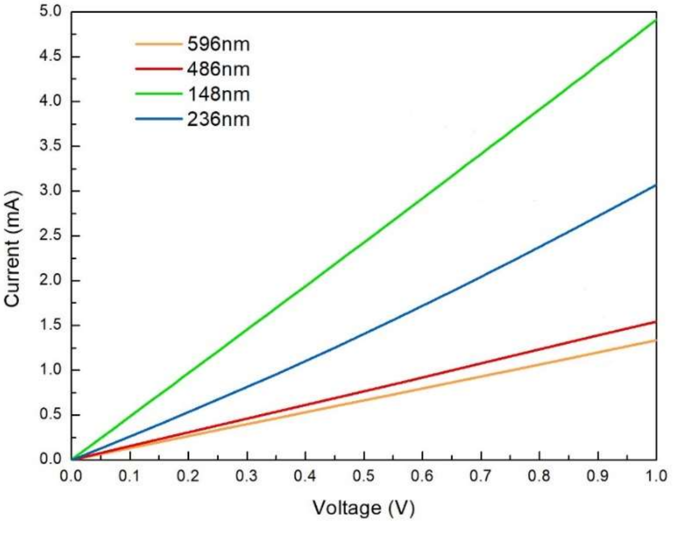

Figure 3 Ohmic V-I charactestics of Ti/a-BC:H(n)/Ti structures of varying a-BC:H(n) thicknesses